## P-Channel 30-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

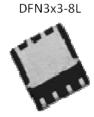
### **Typical Applications:**

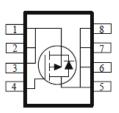
- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY     |                             |                    |  |  |
|---------------------|-----------------------------|--------------------|--|--|
| V <sub>DS</sub> (V) | $r_{DS(on)}(m\Omega)$       | I <sub>D</sub> (A) |  |  |
| -30                 | 20 @ V <sub>GS</sub> = -10V | -10.9              |  |  |
| -30                 | $36 @ V_{GS} = -4.5V$       | -8.1               |  |  |



FREE





| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED) |                      |                   |            |       |  |  |
|---|----------------------|-------------------|------------|-------|--|--|
| Parameter   |                      | Symbol            | Limit      | Units |  |  |
| Drain-Source Voltage  | $V_{DS}$             | -30               | V          |       |  |  |
| Gate-Source Voltage   |                      |                   |            | V     |  |  |
| Continuous Dusin Commenta   | T <sub>A</sub> =25°C | 1                 | -10.9      |       |  |  |
| Continuous Drain Current <sup>a</sup>                                   | T <sub>A</sub> =70°C | l <sub>D</sub>    | -8.2       | Α     |  |  |
| Pulsed Drain Current <sup>b</sup>                                       | -                    | I <sub>DM</sub>   | -50        |       |  |  |
| Continuous Source Current (Diode Conduction) a                          |                      | I <sub>S</sub>    | -3.6       | Α     |  |  |
| Device Discipation 8  | T <sub>A</sub> =25°C |                   | 3.5        | W     |  |  |
| Power Dissipation <sup>a</sup>  | T <sub>A</sub> =70°C | T FD              | 2          | VV    |  |  |
| Operating Junction and Storage Temperature Range                        | -                    | $T_J$ , $T_{stq}$ | -55 to 150 | °C    |  |  |

| THERMAL RESISTANCE RATINGS               |              |                 |       |      |  |  |  |
|--|--------------|-----------------|-------|------|--|--|--|
| Parameter                                | Symbol       | Maximum         | Units |      |  |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | t <= 10 sec  | $R_{\theta JA}$ | 35    | °C/W |  |  |  |
| IMAXIMUM Sunction-to-Ambient             | Steady State | IΛθJA           | 81    | C/VV |  |  |  |

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

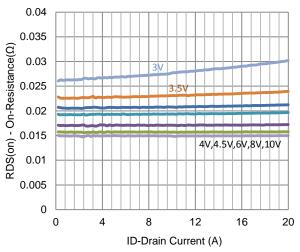
| Parameter                       | Symbol              | Test Conditions  | Min | Тур   | Max  | Unit  |  |
|---------------------------------|---------------------|--|-----|-------|------|-------|--|
| Static                          |                     |  |     |       |      |       |  |
| Gate-Source Threshold Voltage   | $V_{GS(th)}$        | $V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$                                 | -1  |       |      | V     |  |
| Gate-Body Leakage               | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                          |     |       | ±100 | nA    |  |
| Zero Gate Voltage Drain Current |                     | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$                             |     |       | -1   | uA    |  |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>    | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ |     |       | -25  |       |  |
| On-State Drain Current          | I <sub>D(on)</sub>  | $V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$                            | -20 |       |      | Α     |  |
| Drain-Source On-Resistance      | r                   | $V_{GS} = -10 \text{ V}, I_D = -8.7 \text{ A}$                             |     |       | 20   | mΩ    |  |
| Dialii-Source Oil-Resistance    | r <sub>DS(on)</sub> | $V_{GS} = -4.5 \text{ V}, I_D = -6.5 \text{ A}$                            |     |       | 36   | 11177 |  |
| Forward Transconductance        | g <sub>fs</sub>     | $V_{DS} = -15 \text{ V}, I_{D} = -8.7 \text{ A}$                           |     | 15    |      | S     |  |
| Diode Forward Voltage           | $V_{SD}$            | $I_S = -1.8 \text{ A}, V_{GS} = 0 \text{ V}$                               |     | -0.72 |      | V     |  |
|                                 |                     | Dynamic  |     |       |      |       |  |
| Total Gate Charge               | $Q_g$               | $V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$                         |     | 32    |      | nC    |  |
| Gate-Source Charge              | $Q_{gs}$            | $I_{D} = -8.7 \text{ A}$   |     | 7.8   |      |       |  |
| Gate-Drain Charge               | $Q_gd$              | 1 <sub>D</sub> = 0.7 A   |     | 13    |      |       |  |
| Turn-On Delay Time              | t <sub>d(on)</sub>  | $V_{DS} = -15 \text{ V}, R_1 = 1.8 \Omega,$                                |     | 8     |      |       |  |
| Rise Time                       | t <sub>r</sub>      | $V_{DS} = -13 \text{ V}, K_L - 1.8 \Omega,$ $I_D = -8.7 \text{ A},$        |     | 39    |      | ne    |  |
| Turn-Off Delay Time             | $t_{d(off)}$        | $V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$                              |     | 93    |      | ns    |  |
| Fall Time                       | t <sub>f</sub>      | V GEN - 10 V, T GEN - 0 12   |     | 53    |      |       |  |
| Input Capacitance               | C <sub>iss</sub>    |  |     | 1934  |      |       |  |
| Output Capacitance              | C <sub>oss</sub>    | $V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$          |     | 252   |      | pF    |  |
| Reverse Transfer Capacitance    | $C_{rss}$           |  |     | 226   |      |       |  |

#### Notes

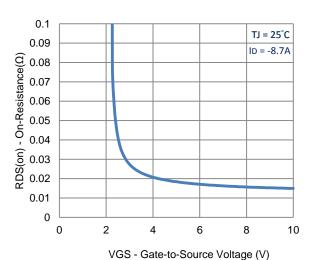
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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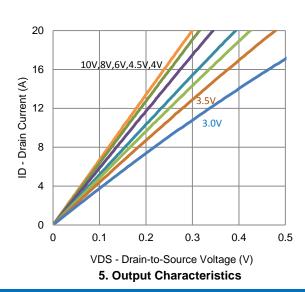
### **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



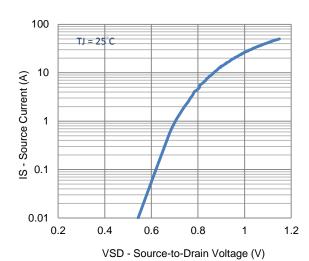
20
TJ = 25°C

16
(4)
Tuesun 12

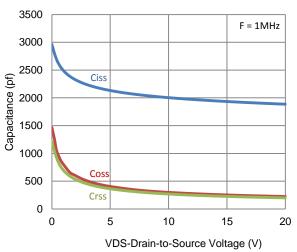
4
0
0
1 2 3 4

VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

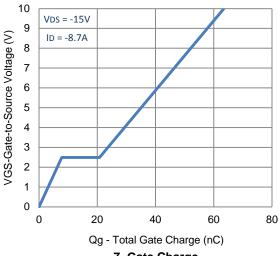


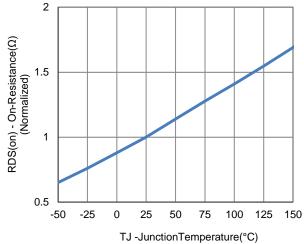
4. Drain-to-Source Forward Voltage



6. Capacitance

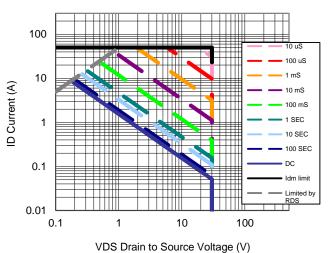
### **Typical Electrical Characteristics**

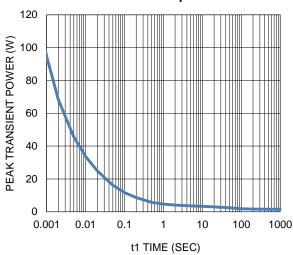




7. Gate Charge

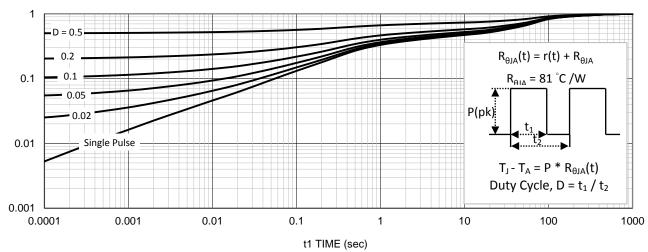






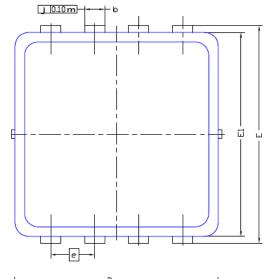
9. Safe Operating Area

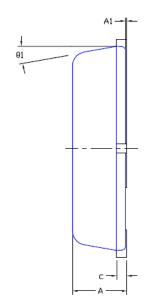
10. Single Pulse Maximum Power Dissipation

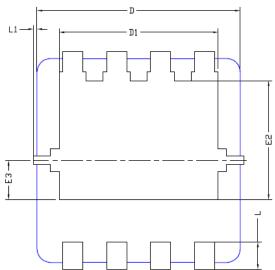


11. Normalized Thermal Transient Junction to Ambient

# Package Information







| DIM, | MILLIMETERS |       |       | INCHES    |        |        |  |
|------|-------------|-------|-------|-----------|--------|--------|--|
| TIM  | ΜIN         | NDM   | MAX   | MIN       | NDM    | MAX    |  |
| Α    | 0,700       | 0,80  | 0.900 | 0,0276    | 0,0315 | 0.0354 |  |
| A1   | 0.00        |       | 0,05  | 0,000     |        | 0'005  |  |
| b    | 0.24        | 0.30  | 0.35  | 0.009     | 0.012  | 0.014  |  |
| С    | 0.10        | 0.152 | 0.25  | 0.004     | 0.006  | 0.010  |  |
| D    | 3.00 BSC    |       |       | 0.118 BSC |        |        |  |
| D1   | 2,35 BSC    |       |       | 0.093 BSC |        |        |  |
| Ε    | 3.20 BSC    |       |       | 0.126 BSC |        |        |  |
| E1   | 3.00 B2C    |       |       | 0.118 BSC |        |        |  |
| E2   | 1.75 BSC    |       |       | 0.069 BSC |        |        |  |
| E3   | 0,575 BSC   |       |       | 0.023 BSC |        |        |  |
| е    | 0,65 BSC    |       |       | 0.026 B2C |        |        |  |
| L    | 0,30        | 0,40  | 0,50  | 0,0118    | 0.0157 | 0.0197 |  |
| L1   | 0           |       | 0.100 | 0         |        | 0,004  |  |
| 91   | 0°          | 10°   | 12°   | 0°        | 10°    | 12°    |  |